

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6050KA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

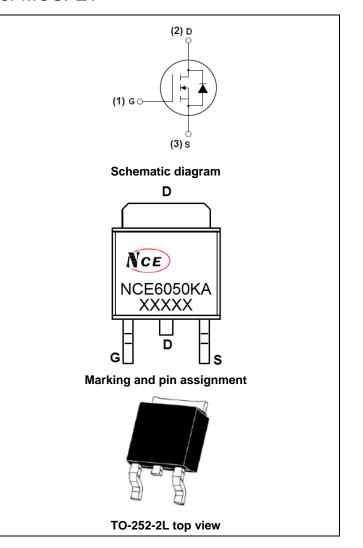
- $V_{DS} = 60V, I_D = 50A$ $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE6050KA	NCE6050KA	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	50	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	35.4	Α
Pulsed Drain Current	I _{DM}	200	Α
Maximum Power Dissipation	P _D	85	W
Derating factor		0.57	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	300	mJ
Operating Junction and Storage Temperature Range	T_J, T_STG	-55 To 175	$^{\circ}$ C

NCE6050KA

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	1.8	°C/W	1
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Electrical Characteristics (Tc=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
rain-Source Breakdown Voltage BV _{DSS} V _{GS} =0V		V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.4	1.9	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	14	20	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	18	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	// -20/// -0//	-	2050	-	PF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	158	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WIFIZ	-	120	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t _{d(on)}		-	15	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =6.7 Ω	-	20	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =5 V , R_{G} =3 Ω	-	120	-	nS
Turn-Off Fall Time	t _f		-	15.6	-	nS
Turn-on Delay Time	t _{d(on)}		-	7.4	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =6.7 Ω	-	5.1	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	28.2	-	nS
Turn-Off Fall Time	t _f		-	5.5	-	nS
Total Gate Charge	Qg	V -20VI -20A	-	50		nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_{D} =20A, V_{GS} =10V	-	6		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	15		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	50	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =20A	-	28	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	40	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+L				y LS+LD)

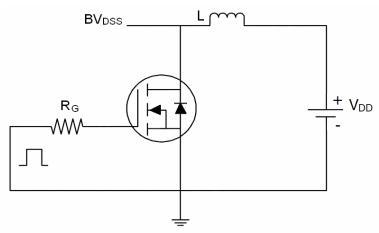
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=30V,V_G=10V,L=0.5mH,Rg=25 Ω

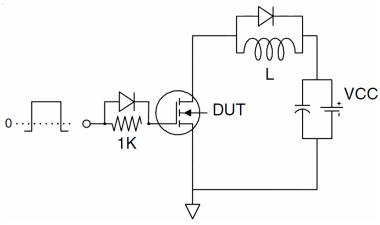


Test Circuit

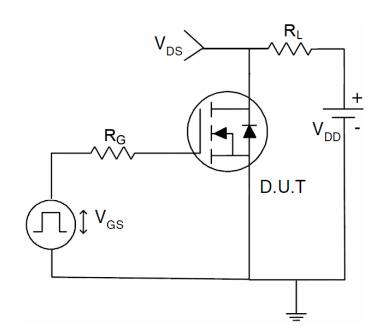
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

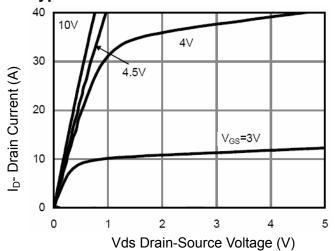


Figure 1 Output Characteristics

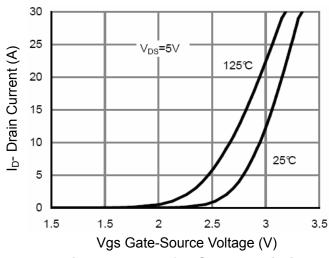


Figure 2 Transfer Characteristics

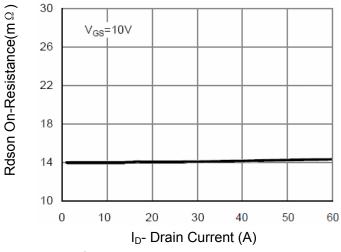


Figure 3 Rdson- Drain Current

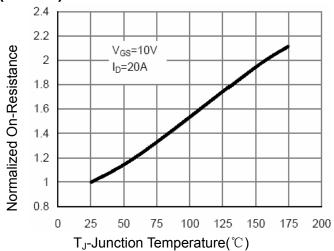


Figure 4 Rdson-Junction Temperature

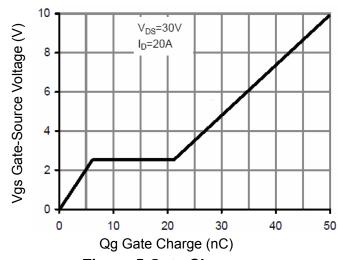


Figure 5 Gate Charge

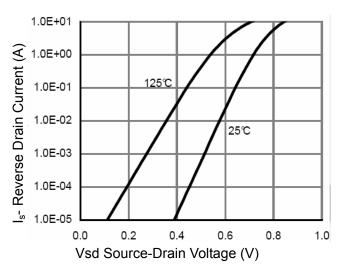


Figure 6 Source- Drain Diode Forward



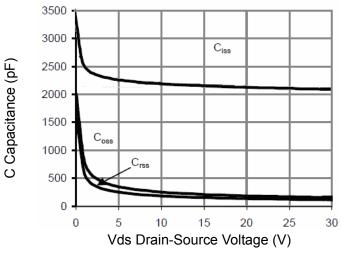


Figure 7 Capacitance vs Vds

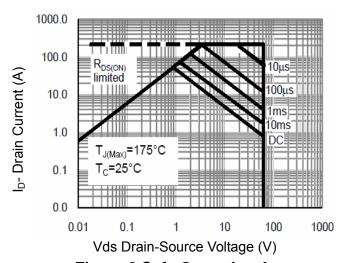


Figure 8 Safe Operation Area

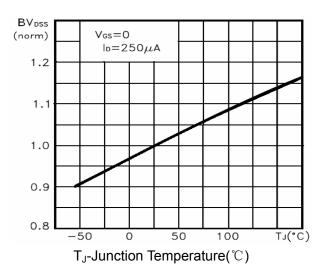


Figure 9 BV_{DSS} vs Junction Temperature

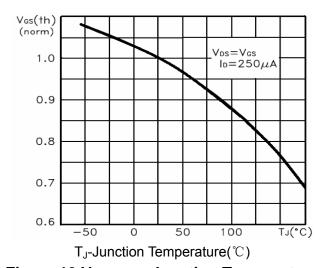


Figure 10 $V_{\text{GS(th)}}$ vs Junction Temperature

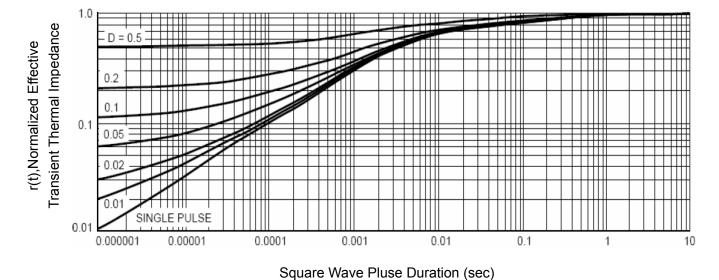
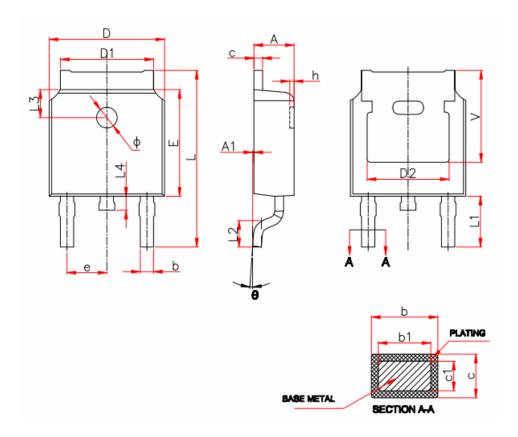


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Millimeters			
Symbol	Min.	Max.		
Α	2.20	2.40		
A1	0.00	0.13		
b	0.66	0.86		
b1	0.73	0.79		
С	0.46	0.58		
c1	0.50	0.52		
D	6.50	6.70		
D1	5.10	5.46		
D2	4.83 REF.			
E	6.00	6.20		
е	2.19	2.39		
L	9.80	10.40		
L1	2.90 REF.			
L2	1.40	1.70		
L3	1.60 REF.			
L4	0.60	1.00		
Ф	1.10	1.30		
θ	0°	8°		

http://www.ncepower.com

NCE6050KA

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